

FDD306P

P-Channel 1.8V Specified PowerTrench® MOSFET

Features

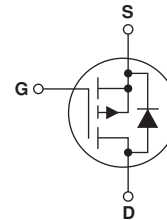
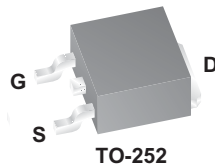
- -6.7 A, -12 V. $R_{DS(ON)} = 28\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
 $R_{DS(ON)} = 41\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$
 $R_{DS(ON)} = 90\text{ m}\Omega @ V_{GS} = -1.8\text{ V}$
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability

Applications

- DC/DC converter

General Description

This P-Channel 1.8V Specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management.



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|--------------------------------|---|-------------|--------------------|
| V_{DSS} | Drain-Source Voltage | -12 | V |
| V_{GSS} | Gate-Source Voltage | ± 8 | V |
| I_D | Drain Current – Continuous (Note 3) | -6.7 | A |
| | – Pulsed (Note 1a) | -54 | |
| P_D | Power Dissipation for Single Operation (Note 1) | 52 | W |
| | (Note 1a) | 3.8 | |
| | (Note 1b) | 1.6 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +175 | $^\circ\text{C}$ |
| Thermal Characteristics | | | |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Note 1) | 2.9 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a) | 40 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1b) | 96 | $^\circ\text{C/W}$ |

Package Marking and Ordering Information

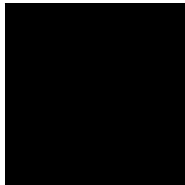
| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|---------|-----------|------------|------------|
| FDD306P | FDD306P | 13" | 12mm | 2500 units |

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|------|----------------------|----------------|----------------------|
| Off Characteristics | | | | | | |
| BV_{DSS} | Drain–Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$ | -12 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\ \mu\text{A}$, Referenced to 25°C | | -0.6 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}$ | | | -1 | μA |
| I_{GSSF} | Gate–Body Leakage | $V_{GS} = \pm 8\text{ V}, V_{DS} = 0\text{ V}$ | | | ± 100 | nA |
| On Characteristics (Note 2) | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$ | -0.4 | -0.5 | -1.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = -250\ \mu\text{A}$, Referenced to 25°C | | 2.2 | | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS} = -4.5\text{ V}, I_D = -6.7\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -6.1\text{ A}$ $V_{GS} = -1.8\text{ V}, I_D = -4.8\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -6.7\text{ A}, T_J = 125^\circ\text{C}$ | | 21 29 42 25 | 28 41 90 | m Ω |
| $I_{D(on)}$ | On–State Drain Current | $V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$ | -45 | | | A |
| g_{FS} | Forward Transconductance | $V_{DS} = -5\text{ V}, I_D = -6.7\text{ A}$ | | 22 | | S |
| Dynamic Characteristics | | | | | | |
| C_{iss} | Input Capacitance | $V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$ | | 1290 | | pF |
| C_{oss} | Output Capacitance | | | 590 | | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 430 | | pF |
| R_G | Gate Resistance | $V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$ | | 4.2 | | Ω |
| Switching Characteristics (Note 2) | | | | | | |
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD} = -6\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$ | | 16 | 29 | ns |
| t_r | Turn–On Rise Time | | | 8 | 16 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time | | | 34 | 54 | ns |
| t_f | Turn–Off Fall Time | | | 41 | 65 | ns |
| Q_g | Total Gate Charge | $V_{DS} = -6\text{ V}, I_D = -6.7\text{ A},$ $V_{GS} = -4.5\text{ V}$ | | 15 | 21 | nC |
| Q_{gs} | Gate–Source Charge | | | 2.0 | | nC |
| Q_{gd} | Gate–Drain Charge | | | 4.4 | | nC |
| Drain–Source Diode Characteristics and Maximum Ratings | | | | | | |
| I_S | Maximum Continuous Drain–Source Diode Forward Current | | | | -3.2 | A |
| V_{SD} | Drain–Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = -3.2\text{ A}$ (Note 2) | | -0.8 | -1.2 | V |
| T_{rr} | Diode Reverse Recovery Time | $I_F = -6.7\text{ A},$ $diF/dt = 100\text{ A}/\mu\text{s}$ (Note 3) | | 37 | | ns |
| I_{rm} | Diode Reverse Recovery Current | | | 0.9 | | A |
| Q_{rr} | Diode Reverse Recovery Charge | | | 17 | | nC |

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $R_{\theta JA} = 40^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper



b) $R_{\theta JA} = 96^\circ\text{C}/\text{W}$ when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

3. Maximum current is calculated as: $\sqrt{\frac{P_D}{R_{DS(on)}}}$ where P_D is maximum power dissipation at $T_C = 25^\circ\text{C}$ and $R_{DS(on)}$ is at $T_J(\text{max})$ and $V_{GS} = 10\text{ V}$.

4. Starting $T_J = 25^\circ\text{C}$, $L = \text{TBD}$, $I_{AS} = -6.7\text{ A}$

Typical Characteristics

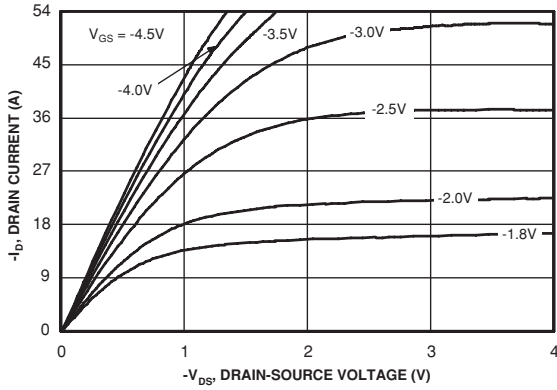


Figure 1. On-Region Characteristics.

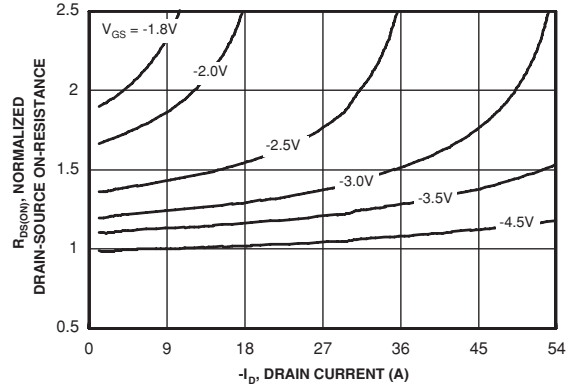


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

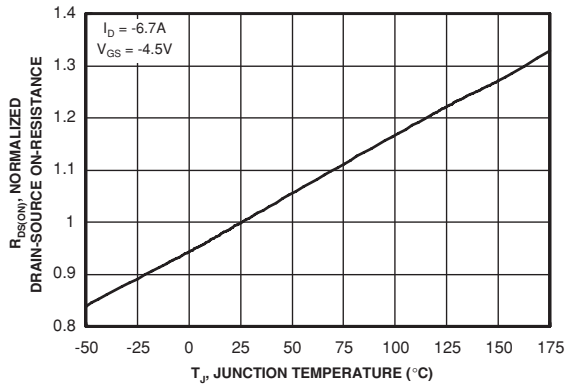


Figure 3. On-Resistance Variation with Temperature.

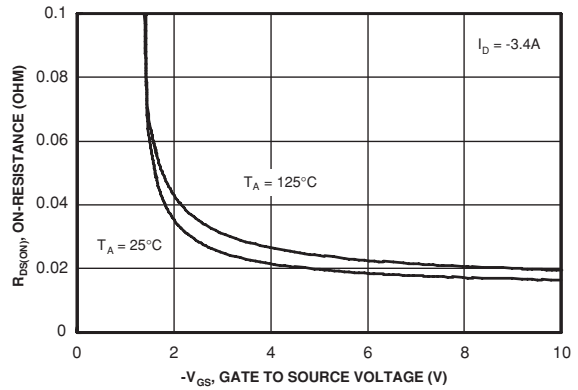


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

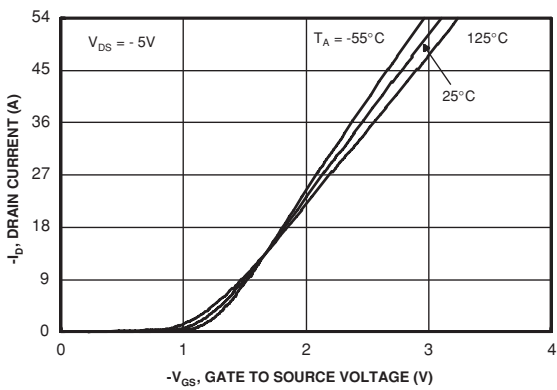


Figure 5. Transfer Characteristics.

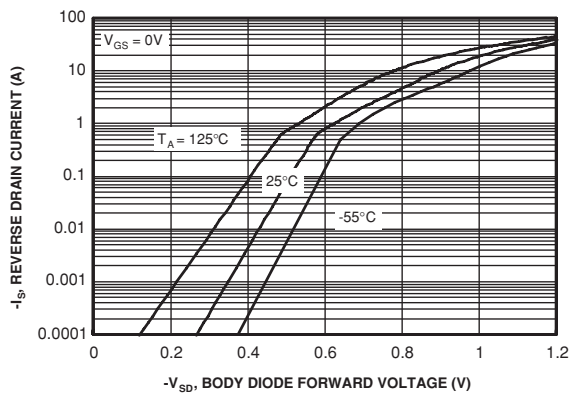


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

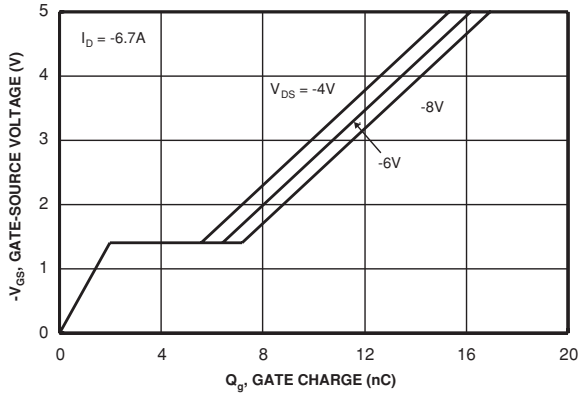


Figure 7. Gate Charge Characteristics.

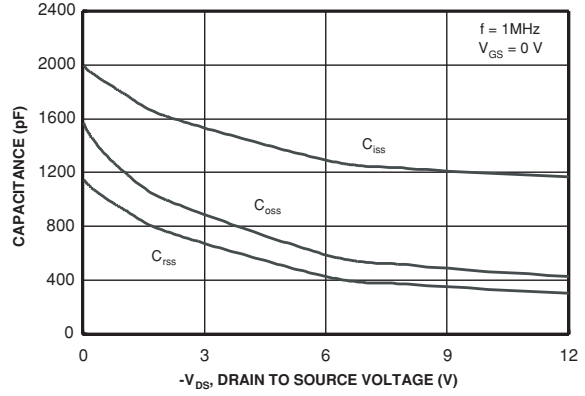


Figure 8. Capacitance Characteristics.

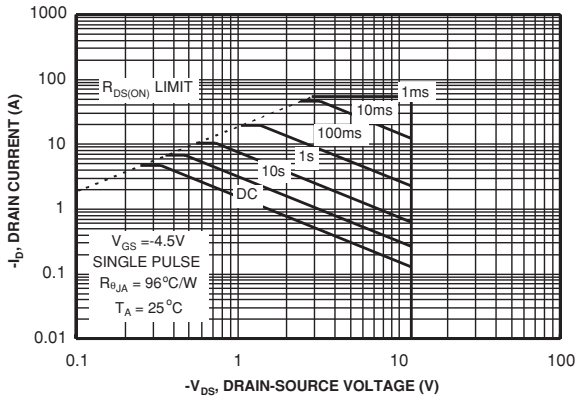


Figure 9. Maximum Safe Operating Area.

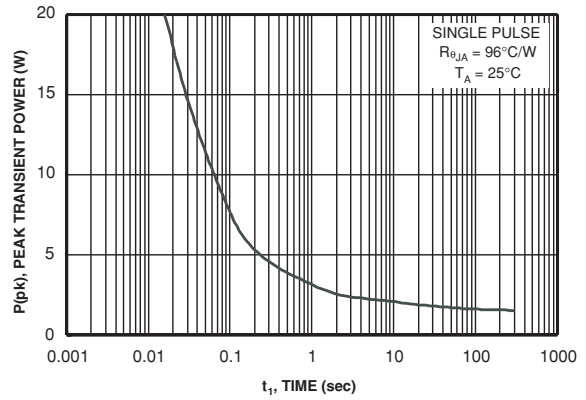


Figure 10. Single Pulse Maximum Power Dissipation.

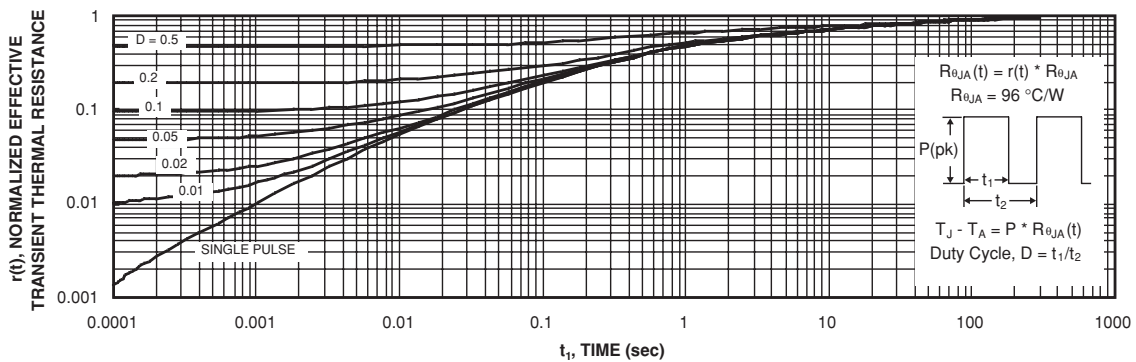


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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